Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Leadless ultra small and ultra thin SMD plastic package 1.1 x 1.0 x 0.37 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V		
V_{GS}	gate-source voltage			-20	-	20	V		
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C		-	-	330	mA		
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	260	mA		
Static characte	Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.2	2.8	Ω		

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	5 7 7	D1 D2
2	G1	gate TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix}$	
3	D2	drain TR2	2 5	G1 $G2$ $G2$
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa256
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

6. Ordering information

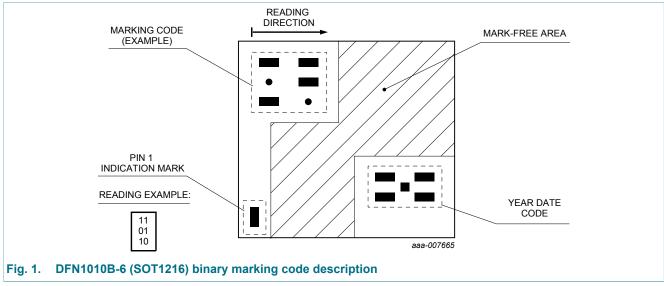
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX7002BKXB	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

7. Marking

Table 4. Marking codes

Type number	Marking code
NX7002BKXB	00 01 01



NX7002BKXB

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{sp} = 25 °C		-	330	mA
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	260	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	170	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.8	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	285	mW
			[1]	-	407	mW
		T _{sp} = 25 °C		-	4032	mW
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	[1]	-	0.2	Α
Per device						
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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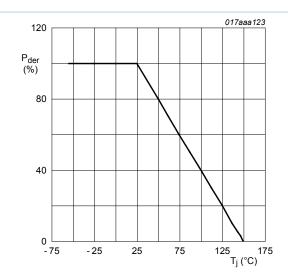


Fig. 2. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

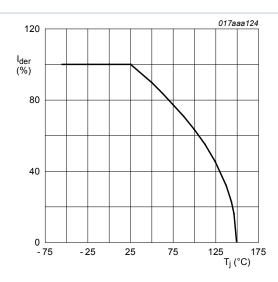
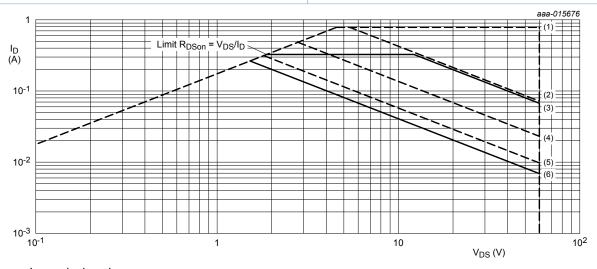


Fig. 3. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



 I_{DM} = single pulse

(1)
$$t_p = 10 \mu s$$

(2)
$$t_p = 1 \text{ ms}$$

(3) DC;
$$T_{sp}$$
 = 25 °C

$$(4) t_p = 10 ms$$

$$(5) t_p = 100 \text{ ms}$$

(6) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

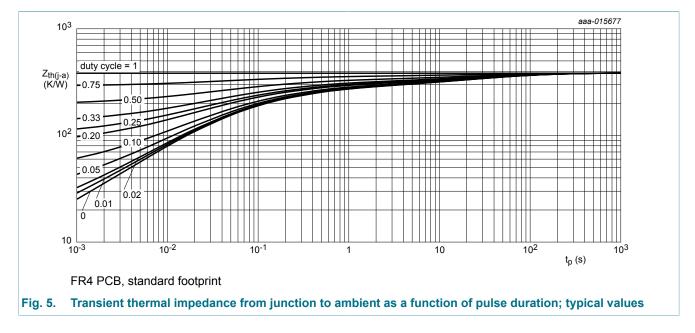
Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

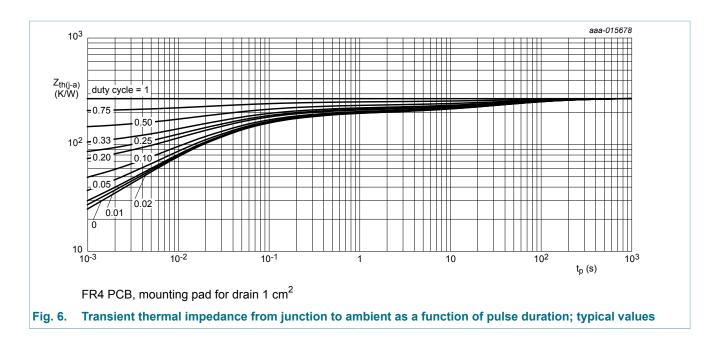
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	276	307	K/W
		[2]	-	381	438	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	27	31	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)		·			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μA
R _{DSon} drain-source resistance	drain-source on-state	V _{GS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	2.2	2.8	Ω
	resistance	V _{GS} = 10 V; I _D = 200 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.5	3.2	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; T _j = 25 °C	-	600	-	mS
R_G	gate resistance	f = 1 MHz	-	2.5	-	Ω
Dynamic c	haracteristics (per transist	or)				,
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 200 mA; V _{GS} = 10 V;	-	1	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; I _D = 200 mA; V _{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time		-	6.9	-	ns
t _f	fall time		-	2.9	-	ns
Source-dra	ain diode (per transistor)		'	'		,
V_{SD}	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.87	1.2	V

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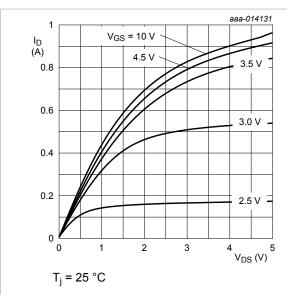
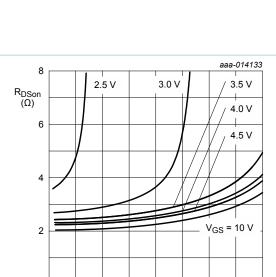


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

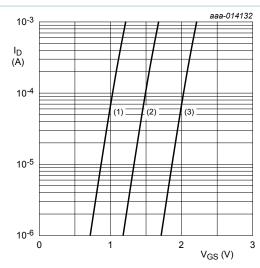


 $T_j = 25 \,^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

0.4

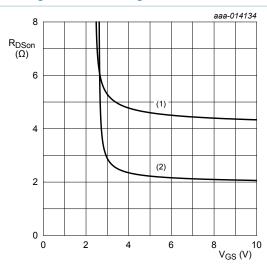
0.8



$$T_j = 25 \,^{\circ}\text{C}; \, V_{DS} = 5 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 0.2 A$

(1) $T_i = 150 \,^{\circ}\text{C}$

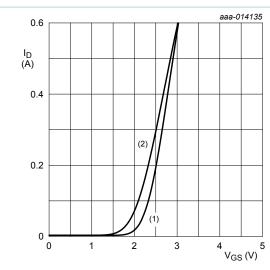
(2) $T_i = 25 \, ^{\circ}C$

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

2.5

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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_i = 25 \, ^{\circ}C$

(2) $T_j = 150 \, ^{\circ}C$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

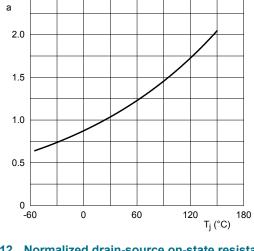
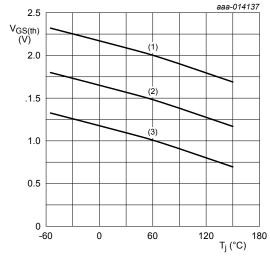


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

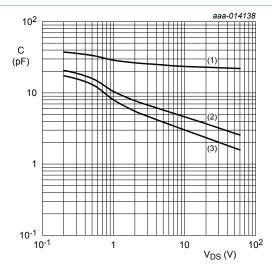
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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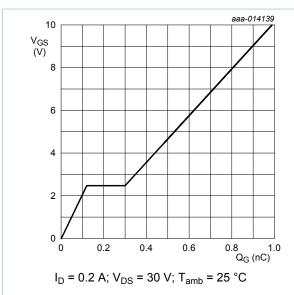


Fig. 15. Gate-source voltage as a function of gate charge; typical values

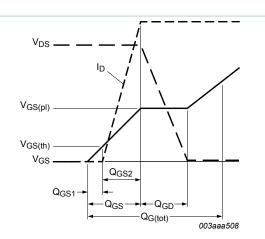
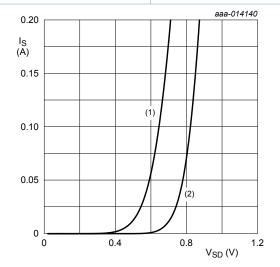


Fig. 16. MOSFET transistor: Gate charge waveform definitions



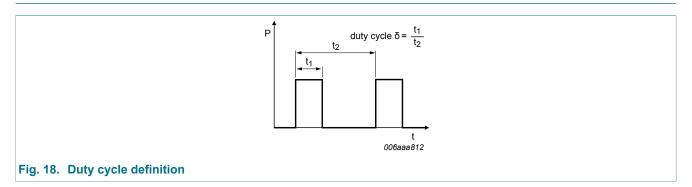
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

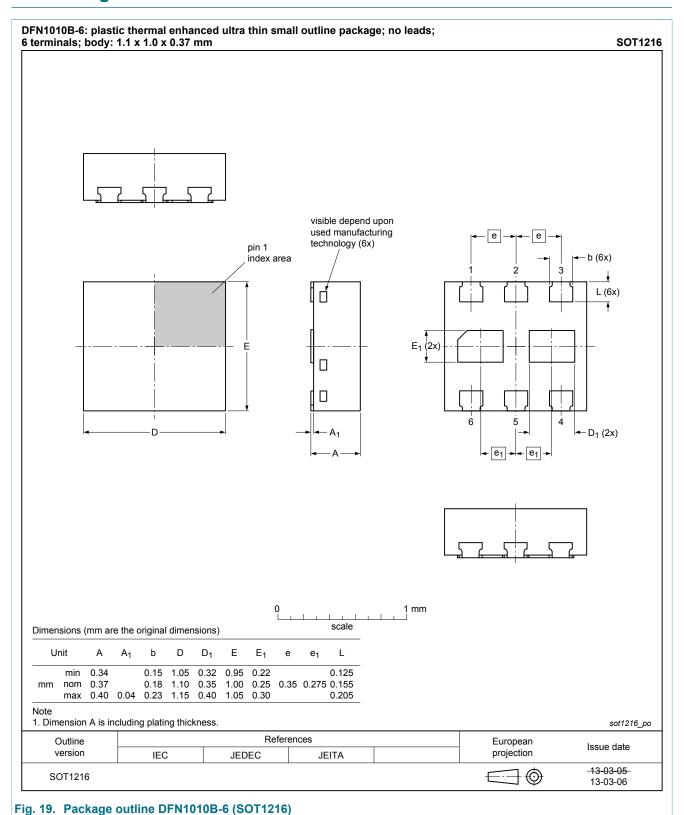
Fig. 17. Source current as a function of source-drain voltage; typical values

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11. Test information



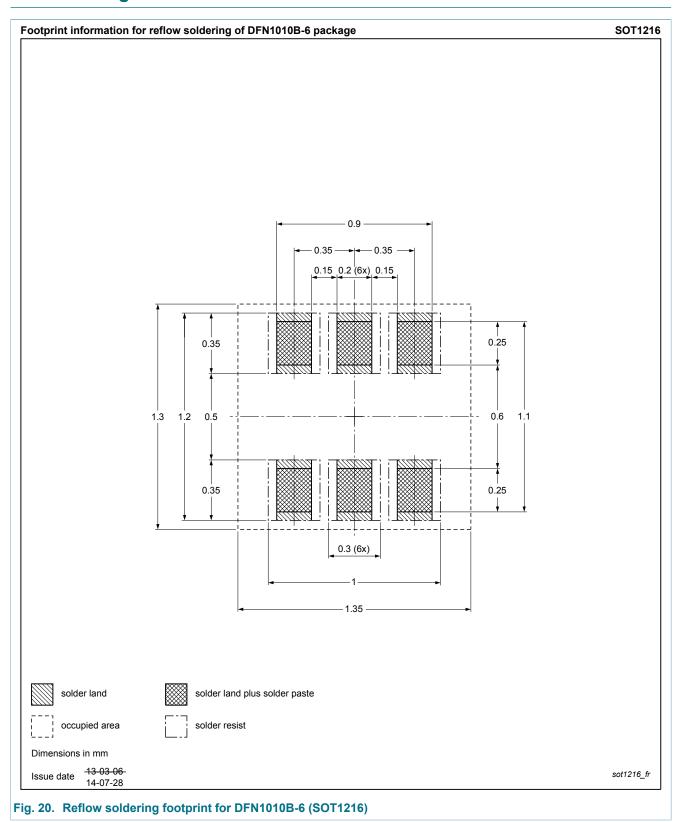
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
NX7002BKXB v.2	20150630	Product data sheet	-	NX7002BKXB v.1		
Modification:	Change of binary marking code position					
NX7002BKXB v.1	20141210	Product data sheet	-	-		

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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